

# LED CHIP CN850-40P

## SPECIFICATION OF LED CHIP CN850-40P [INFRARED]

### 1) Commodity Type and Physical Characteristics.

- |                      |                     |                             |
|----------------------|---------------------|-----------------------------|
| 1. Material          | GaAlAs/GaAlAs (DDH) |                             |
| 2. Electrode         | Top Side            | P (anode) side : Au Alloy   |
|                      | Bottom Side         | N (cathode) side : Au Alloy |
| 3. Electrode Pattern | Fig.1               |                             |
| 4. Chip Size         | Fig.2               |                             |
| 5. Chip Thickness    | Fig.2               |                             |
| 6. Emission Area     | Fig.2               |                             |

### 2) Electro-Optical Characteristics

Parameters	Symbol	Condition	min.	typ.	max.	unit
Forward Voltage	Vf	If=20mA		1.4	1.6	V
Reverse Current	Ir	Vr=5V			10	uA
Power Intensity	Po	If=20mA	3.0	5.0		mW
Peak Wavelength	λ P	If=20mA	840	850	860	nm
Spectral Radiation Bandwidth	DI	If=20mA		35		nm
RiseTime	tr	If=20mA		30		ns
FallTime	tf	If=20mA		25		ns

‡ Die shall be mounted on TO=18 gold header without resin coated.(Ta=25°C)

[Unit : um]

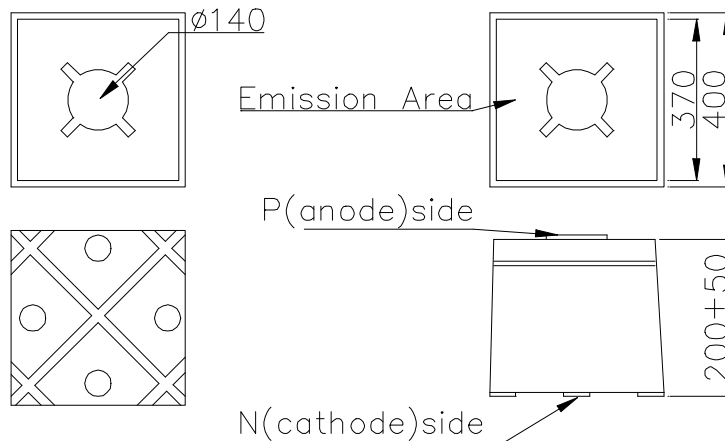


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area